

1201.63407

## PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Munir H. Nayfeh  
 Serial No.: 09/496,506  
 Conf. No.: 6344  
 Filed: February 2, 2000  
 For: SILICON NANOPARTICLE FIELD EFFECT  
 TRANSISTOR AND TRANSISTOR  
 MEMORY DEVICE  
 Art Unit: 2811  
 Examiner: Sara R. Crane

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AMENDMENT F

Commissioner of Patents  
 P.O. Box 1450  
 Alexandria, VA 22313-1450

Dear Sir:

In response to the Final Office Action mailed November 4, 2003, please consider the following Remarks.

REMARKS

Claims 5-7 stand rejected under 35 U.S.C. §112, first paragraph, as failing to comply with the enablement requirement. Particularly, the office action states that "single particle tunneling as explicitly set forth in claims 5-7 has not been shown, and would require undue experimentation to produce." Applicants respectfully traverse this statement and the rejection, as all features defined in claims 5-7 are believed to be clearly supported in the present specification and drawings.

In response to Applicants' previous response regarding claims 5-7, the office action states:

Applicant has not shown that single particle tunneling can be obtained by the method of these claims. Sketches are not experimental results. Whether this phenomenon can be obtained in a particular experimental set-up is not predictable in nature and undue experimentation would be required to generalize the results of Applicant's figure 1 to produce a transistor having the regions recited in the claims. Have any experimental results been